## Nikos Konofaos

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Electrical characterisation of SiON/n-Si structures for MOS VLSI electronics. Microelectronics Journal, 2004, 35, 421-425.	2.0	74
2	Electrical properties of SrTiO3 thin films on Si deposited by magnetron sputtering at low temperature. Applied Physics Letters, 2001, 79, 1513-1515.	3.3	53
3	Reduced molybdenum oxide as an efficient electron injection layer in polymer light-emitting diodes. Applied Physics Letters, 2011, 98, 123301.	3.3	49
4	Dielectric properties and electronic transitions of porous and nanostructured cerium oxide films. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 109, 69-73.	3.5	42
5	Characterisation of the Interface States between Amorphous Diamond-Like Carbon Films and (100) Silicon. Physica Status Solidi A, 1997, 161, 111-123.	1.7	41
6	Electrical characterization of the SiON/Si interface for applications on optical and MOS devices. Semiconductor Science and Technology, 2003, 18, 56-59.	2.0	41
7	Tungsten oxides as interfacial layers for improved performance in hybrid optoelectronic devices. Thin Solid Films, 2011, 519, 5748-5753.	1.8	38
8	Characterization of heterojunction devices constructed by amorphous diamondlike films on silicon. Journal of Applied Physics, 1997, 81, 6238-6245.	2.5	36
9	Dielectric properties of CVD grown SiON thin films on Si for MOS microelectronic devices. Semiconductor Science and Technology, 2004, 19, 50-53.	2.0	29
10	Amorphous diamondlike carbonâ€silicon heterojunction devices formed by ion implantation. Applied Physics Letters, 1992, 61, 2805-2807.	3.3	25
11	Properties and density of states of the interface between silicon and carbon films rich in sp3 bonds. Journal of Applied Physics, 1997, 82, 5017-5020.	2.5	25
12	Characterisation of the BaTiO3/p-Si interface and applications. Applied Surface Science, 2000, 166, 504-507.	6.1	25
13	Rare earth oxides as high-k dielectrics for Ge based MOS devices: An electrical study of Pt/Gd2O3/Ge capacitors. Solid-State Electronics, 2007, 51, 164-169.	1.4	23
14	Gate stack dielectric degradation of rare-earth oxides grown on high mobility Ge substrates. Journal of Applied Physics, 2012, 112, .	2.5	23
15	Design of Low-Power High-Performance 2–4 and 4–16 Mixed-Logic Line Decoders. IEEE Transactions on Circuits and Systems II: Express Briefs, 2017, 64, 176-180.	3.0	23
16	Properties of barium titanate (BaTiO <sub>3</sub> ) thin films grown on silicon by rf magnetron sputtering. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 2000, 80, 395-407.	0.6	22
17	Characterization of magnetron sputtering deposited thin films of TiN for use as a metal electrode on TiN/SiO2/Si metal–oxide–semiconductor devices. Journal of Applied Physics, 2000, 88, 7192-7196.	2.5	19
18	Target Localization Utilizing the Success Rate in Infrared Pattern Recognition. IEEE Sensors Journal, 2006, 6, 1355-1364.	4.7	19

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19	Highly porous tungsten oxides for electrochromic applications. Microelectronic Engineering, 2013, 111, 149-153.	2.4	18
20	Lowâ€power highâ€performance CMOS 5â€2 compressor with 58 transistors. Electronics Letters, 2018, 54, 278-280.	1.0	16
21	Î <sup>°</sup> Quantum Pattern Recognition Method for Improving Pairwise Sequence Alignment. Scientific Reports, 2019, 9, 7226.	3.3	16
22	Charge carrier response time in sputtered a-C/n-Si heterojunctions. Applied Physics Letters, 2001, 79, 2381-2383.	3.3	15
23	Electrical characterisation of SrTiO3/Si interfaces. Journal of Non-Crystalline Solids, 2002, 303, 185-189.	3.1	14
24	Device characterization for amorphous diamond-like carbon–silicon heterojunctions. Journal of Applied Physics, 1998, 84, 4634-4636.	2.5	13
25	Formation of stoichiometric, sub-stoichiometric undoped and hydrogen doped tungsten oxide films, enabled by pulsed introduction of O2 or H2 during hot-wire vapor deposition. Thin Solid Films, 2013, 537, 124-130.	1.8	13
26	On the Use of FDTD and Ray-Tracing Schemes in the Nanonetwork Environment. IEEE Communications Letters, 2014, 18, 1823-1826.	4.1	13
27	Crystal quality and conductivity type of (002) ZnO films on (100) Si substrates for device applications. Solid-State Electronics, 2010, 54, 1150-1154.	1.4	12
28	Design and Simulation of 6TSRAM Cell Architectures in 32nm Technology. Journal of Engineering Science and Technology Review, 2016, 9, 145-149.	0.4	11
29	Effect of the layered structure on the electronic properties of amorphous carbon films on n-Si. Journal of Applied Physics, 1999, 86, 4446-4451.	2.5	10
30	Electrical behaviour of metal/a-C/Si and metal/CN/Si devices. Carbon, 1999, 37, 871-876.	10.3	10
31	Characterization of BaTiO3 thin films on p-Si. Materials Science in Semiconductor Processing, 2001, 4, 305-307.	4.0	10
32	Electrical characterization of TiN/a-C/Si devices grown by magnetron sputtering at room temperature. Applied Physics Letters, 2001, 78, 1682-1684.	3.3	9
33	Design, simulation and performance evaluation of a single-electron 2-4 decoder. Microelectronics Journal, 2008, 39, 1613-1621.	2.0	9
34	Reduced transition metal oxides as electron injection layers in hybrid-PLEDs. Microelectronic Engineering, 2012, 90, 59-61.	2.4	9
35	Low-power, high-performance 64-bit CMOS priority encoder using static-dynamic parallel architecture. , 2016, , .		9
36	Organic photovoltaic performance improvement using atomic layer deposited ZnO electron-collecting layers. Solid-State Electronics, 2014, 101, 50-56.	1.4	8

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37	New evidence on the relation between tunnelling and trap density at insulator/semiconductor interfaces. Semiconductor Science and Technology, 2001, 16, 733-738.	2.0	7
38	Electrical properties of carbon nitride films on silicon. Journal of Applied Physics, 2002, 91, 9915.	2.5	7
39	The effects of interface and bulk defects on the electrical performance of amorphous carbon/silicon heterojunctions. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 91-92, 379-383.	3.5	7
40	Using future position restriction rules for stabilizing the results of a noise-sensitive indoor localization system. Optical Engineering, 2007, 46, 067202.	1.0	7
41	Design and Simulation of NAND Gates Made of Single Electron Devices. , 2008, , .		7
42	Design, Simulation and Performance Evaluation of a NAND Based Single-electron 2-4 Decoder. , 2009, , .		7
43	Improving the Sequence Alignment Method by Quantum Multi-Pattern Recognition. , 2018, , .		7
44	Encoding Two-Qubit Logical States and Quantum Operations Using the Energy States of a Physical System. Technologies, 2022, 10, 1.	5.1	7
45	Conductance technique measurements of the density of states between Si and ZnS grown by molecular beam epitaxy. Journal of Applied Physics, 1993, 74, 397-401.	2.5	6
46	Properties of Al–SrTiO <tex>\$_3\$</tex> –ITO Capacitors for Microelectronic Device Applications. IEEE Transactions on Electron Devices, 2004, 51, 1202-1205.	3.0	6
47	Characteristics of SrTiO 3 thin films deposited on Si by rf magnetron sputtering at various substrate temperatures. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 2002, 82, 891-903.	0.6	6
48	Hot-wire substoichiometric tungsten oxide films deposited in hydrogen environment with n-type conductivity. Journal Physics D: Applied Physics, 2012, 45, 445101.	2.8	5
49	High-Performance and Energy-Efficient 256-Bit CMOS Priority Encoder. , 2017, , .		5
50	Electronic transport phenomena in devices containing amorphous diamond-like films on silicon. Solid State Communications, 1998, 105, 257-261.	1.9	4
51	Electrical characterization and carrier transport mechanisms of GaAs p/i/n devices for photovoltaic applications. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 80, 152-155.	3.5	4
52	A complementary single-electron 4-bit multiplexer. , 2010, , .		4
53	Memory performance of MOS structure embedded with laser annealed gold NCs. Solid-State Electronics, 2018, 148, 63-69.	1.4	4
54	Nitrogen induced states at the CN x /Si interface. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 71, 315-320.	3.5	3

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55	Defect related effects on the reliability and performance of an embedded DRAM cell designed with MOSFETs with alternative gate dielectrics. Journal of Physics: Conference Series, 2005, 10, 365-368.	0.4	3
56	Characterization of physical and electrical properties of BaTiO3 films deposited on p-Si by modified polymeric precursors. Journal of Electronic Materials, 2005, 34, 1259-1263.	2.2	3
57	QuCirDET: A design and simulation tool for quantum circuits. , 2016, , .		3
58	PSK OFDM optical wireless communication systems with receiver's diversity over gamma-gamma turbulence channels and spatial jitter. , 2017, , .		3
59	Temperature dependence of the barrier at the tetrahedral amorphous carbon-silicon interface. Semiconductor Science and Technology, 2001, 16, 474-477.	2.0	2
60	<title>Design and simulation of an embedded DRAM cell made up of MOSFETs having alternative gate dielectrics</title> . , 2005, , .		2
61	The peak and average temperature in a self-heated GaN HFET. Solid-State Electronics, 2007, 51, 142-146.	1.4	2
62	Multi field SRAM access via intra-encoders and crossbar addressing scheme. , 2017, , .		2
63	A VHDL implementation of the Hummingbird cryptographic algorithm. , 2017, , .		2
64	Quantum Pattern Recognition for Local Sequence Alignment. , 2017, , .		2
65	Estimation of a Target Position Based on Infrared Pattern Reception Quality. IETE Technical Review (Institution of Electronics and Telecommunication Engineers, India), 2010, 27, 36.	3.2	2
66	Utilising noise effects on infrared pattern reception for position estimation on a grid plane. , 2007, , .		1
67	A methodology for the implementation of MOSFETs with a high-k dielectric gate material on the design of 90 nm technology circuits. International Journal of Electronics, 2008, 95, 333-349.	1.4	1
68	Crystal quality and conductivity type of epitaxial (002) ZnO films on (100) Si substrates for device applications. , 2009, , .		1
69	A four base computational method for the implementation of a quantum computer using silicon devices: Circuit and simulation. Mathematical and Computer Modelling, 2010, 51, 144-149.	2.0	1
70	Ultra-low-power and compact 8-bit CMOS priority encoder. International Journal of Electronics Letters, 2017, 5, 272-278.	1.2	1
71	Crossbar sector addressing scheme on SRAMs. , 2017, , .		1
72	A Quantum Computer Architecture Based on Semiconductor Recombination Statistics. Lecture Notes in Computer Science, 2005, , 582-588.	1.3	1

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73	Utilizing infrared pattern recognition features for indoor localization validated by future position restrictions. , 2006, , .		1
74	Temperature dependence of the electrical properties of MOS devices constructed by sol gel deposited BaTiO3films on p-Si. Journal of Physics: Conference Series, 2005, 10, 49-52.	0.4	0
75	An electrical, optical and electron paramagnetic resonance study of room temperature deposited CNx films on Si. Thin Solid Films, 2005, 482, 270-274.	1.8	0
76	A New Concept On A Quantum Computer Based On Schockley-Read-Hall Recombination Statistics In Microelectronic Devices. AIP Conference Proceedings, 2005, , .	0.4	0
77	A quantum computer based on recombination processes in microelectronic devices. Journal of Physics: Conference Series, 2005, 10, 85-88.	0.4	Ο
78	Modeling and Simulation of Submicron MOSFETs with Alternative Gate Dielectrics for DRAM Cells. , 0, , $\cdot$		0
79	Implementation of a Hadamard Gate Using Laser Light on a Phosphorus Doped Si Device. AlP Conference Proceedings, 2007, , .	0.4	0
80	Studying compatibilities between quantum cellular automata and Kane's semiconductor based quantum computer. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 3865-3867.	0.8	0
81	Developing quantum nanocomputing for pervasive health environments. , 2009, , .		0
82	Electrical reliability characteristics and dielectrics degradation in gate stacks (REO-HfO <inf>2</inf> ) grown on the high mobility Ge substrates. , 2011, , .		0
83	Interface engineering for efficient organic optoelectronic devices using nanostructured transition metal oxides. , 2011, , .		0
84	Quantum noise simulation: A software module for QuCirDET. , 2017, , .		0
85	Design and implementation of quantum circuits for fault-tolerant architectures. , 2017, , .		0
86	High-performance and energy-efficient 64-bit incrementer/decrementer using Multiple-Output Monotonic CMOS. The Integration VLSI Journal, 2018, 62, 270-281.	2.1	0
87	Quantum recovery protocols for stabilizer codes: Deterministic Monte-Carlo simulation. AIP Advances, 2018, 8, .	1.3	0
88	A Quantum Cellular Automata Type Architecture with Quantum Teleportation for Quantum Computing. Entropy, 2019, 21, 1235.	2.2	0
89	Simultaneous accessing of multiple SRAM subregions forming configurable and automatically generated memory fields. International Journal of Circuit Theory and Applications, 2021, 49, 2238-2254.	2.0	0
90	Noise investigation in a spin-based four-qubit GaAs block of self-assembled quantum dots. AIP Advances, 2021, 11, 065126.	1.3	0

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91	A wireless infrared sensor network for the estimation of the position and orientation of a moving target. , 2007, , .		0
92	A Model for Encoding Multiple Logical Qubit States into the Energy Eigenstates of a Transmon System. , 2021, , .		0